



## Description

The HXY6P04MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ . This device is suitable for use as a load switch or in PWM applications.

## General Features

$V_{DS} = -40V, I_D = -6A$

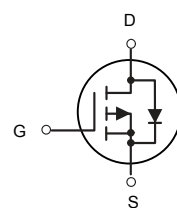
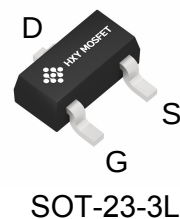
$R_{DS(ON)} < 40m\Omega @ V_{GS} = -10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

## Package Marking and Ordering Information

| Product ID | Pack      | Marking | Qty(PCS) |
|------------|-----------|---------|----------|
| HXY6P04MI  | SOT-23-3L | 230S    | 3000     |

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Symbol          | Parameter                                                  | Limit      | Unit |
|-----------------|------------------------------------------------------------|------------|------|
| $V_{DS}$        | Drain-Source Voltage                                       | -40        | V    |
| $V_{GS}$        | Gate-Source Voltage                                        | $\pm 20$   | V    |
| $I_D$           | Drain Current-Continuous                                   | -6         | A    |
| $I_{D@Ta=70}$   | Drain Current-Continuous                                   | -4.6       | A    |
| $I_{DM}$        | Drain Current-Pulsed (Note 1)                              | -25        | A    |
| $P_D$           | Maximum Power Dissipation                                  | 2.0        | W    |
| $P_{D@Ta=70}$   | Total Power Dissipation <sup>3</sup>                       | 1.5        | W    |
| $T_J, T_{STG}$  | Operating Junction and Storage Temperature Range           | -55 To 150 | °C   |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 2)           | 65         | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s) | 55         | °C/W |



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

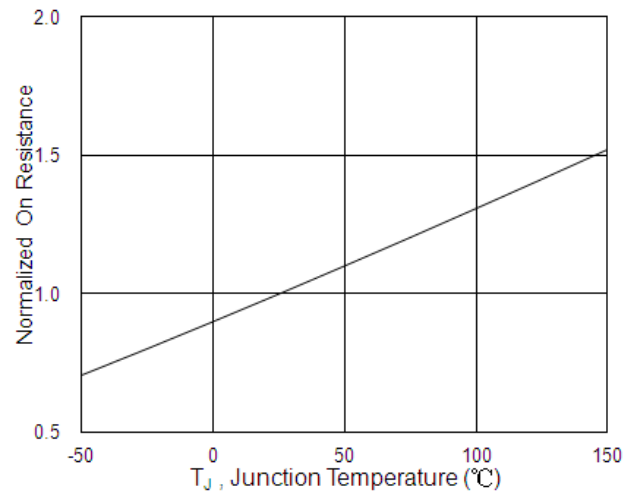
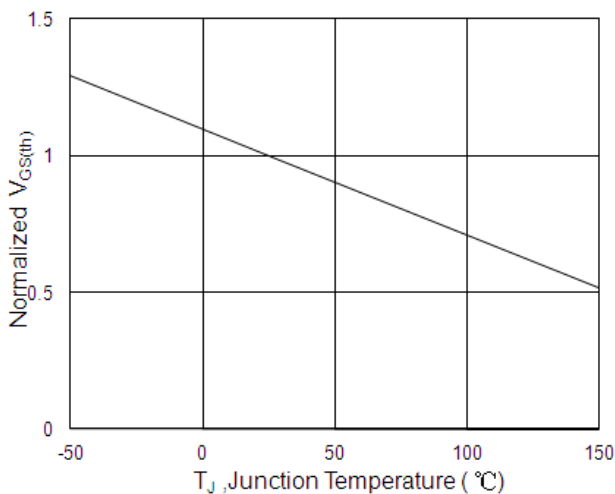
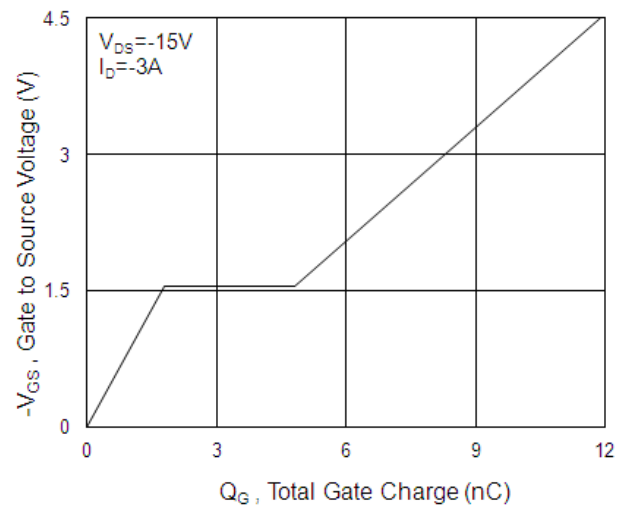
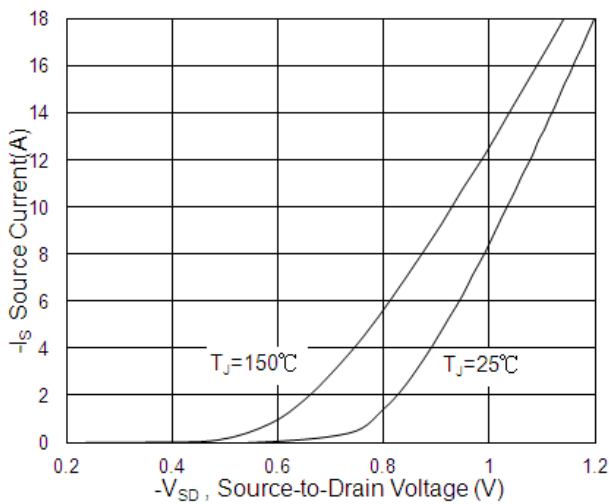
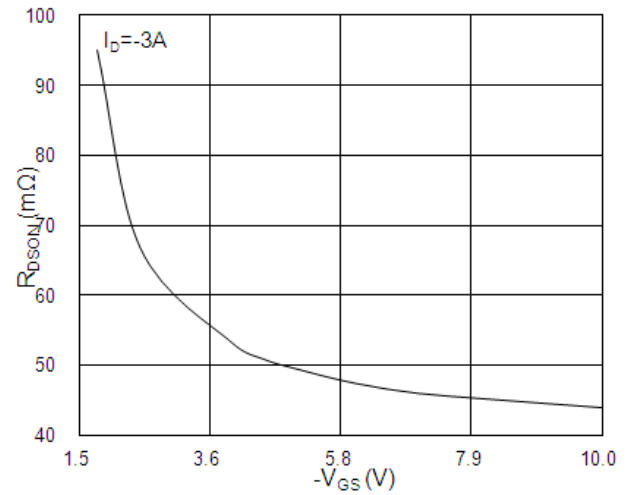
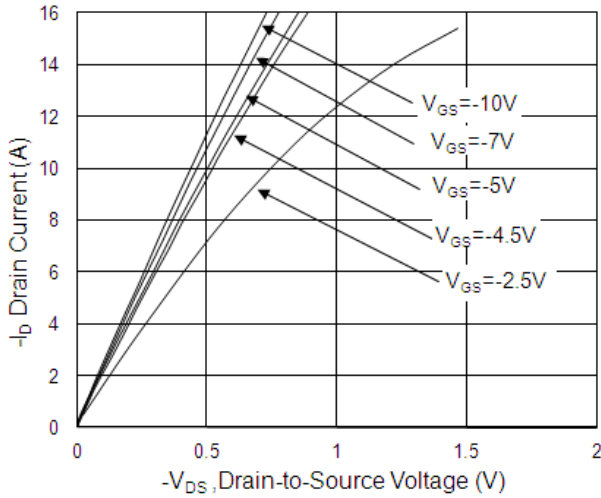
| Symbol                       | Parameter                                      | Conditions                                                      | Min. | Typ.   | Max.      | Unit                 |
|------------------------------|------------------------------------------------|-----------------------------------------------------------------|------|--------|-----------|----------------------|
| $BV_{DSS}$                   | Drain-Source Breakdown Voltage                 | $V_{GS}=0V$ , $I_D=-250\mu A$                                   | -40  | ---    | ---       | V                    |
| $\Delta BV_{DSS}/\Delta T_J$ | $BV_{DSS}$ Temperature Coefficient             | Reference to $25^\circ\text{C}$ , $I_D=-1mA$                    | ---  | -0.014 | ---       | V/ $^\circ\text{C}$  |
| $R_{DS(ON)}$                 | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=-10V$ , $I_D=-3A$                                       | ---  | 34     | 40        | $m\Omega$            |
|                              |                                                | $V_{GS}=-4.5V$ , $I_D=-3A$                                      | ---  | 45     | 60        |                      |
|                              |                                                | $V_{GS}=-2.5V$ , $I_D=-2A$                                      | ---  | ---    | ---       |                      |
| $V_{GS(th)}$                 | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=-250\mu A$                               | -1.0 | ---    | -2.5      | V                    |
| $\Delta V_{GS(th)}$          | $V_{GS(th)}$ Temperature Coefficient           |                                                                 | ---  | 2.6    | ---       | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                    | Drain-Source Leakage Current                   | $V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$            | ---  | ---    | -1        | $\mu A$              |
|                              |                                                | $V_{DS}=-24V$ , $V_{GS}=0V$ , $T_J=55^\circ\text{C}$            | ---  | ---    | -5        |                      |
| $I_{GSS}$                    | Gate-Source Leakage Current                    | $V_{GS}=\pm 12V$ , $V_{DS}=0V$                                  | ---  | ---    | $\pm 100$ | nA                   |
| $g_{fs}$                     | Forward Transconductance                       | $V_{DS}=-5V$ , $I_D=-3A$                                        | ---  | 5.6    | ---       | S                    |
| $Q_g$                        | Total Gate Charge (-4.5V)                      | $V_{DS}=-15V$ , $V_{GS}=-4.5V$ , $I_D=-3A$                      | ---  | 11.9   | ---       | nC                   |
| $Q_{gs}$                     | Gate-Source Charge                             |                                                                 | ---  | 1.8    | ---       |                      |
| $Q_{gd}$                     | Gate-Drain Charge                              |                                                                 | ---  | 3      | ---       |                      |
| $T_{d(on)}$                  | Turn-On Delay Time                             | $V_{DD}=-15V$ , $V_{GS}=-4.5V$ ,<br>$R_G=3.3\Omega$ , $I_D=-3A$ | ---  | 6.6    | ---       | ns                   |
| $T_r$                        | Rise Time                                      |                                                                 | ---  | 27.8   | ---       |                      |
| $T_{d(off)}$                 | Turn-Off Delay Time                            |                                                                 | ---  | 46.2   | ---       |                      |
| $T_f$                        | Fall Time                                      |                                                                 | ---  | 20.6   | ---       |                      |
| $C_{iss}$                    | Input Capacitance                              | $V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1MHz$                          | ---  | 920    | ---       | pF                   |
| $C_{oss}$                    | Output Capacitance                             |                                                                 | ---  | 73     | ---       |                      |
| $C_{rss}$                    | Reverse Transfer Capacitance                   |                                                                 | ---  | 71     | ---       |                      |
| $I_S$                        | Continuous Source Current <sup>1,4</sup>       | $V_G=V_D=0V$ , Force Current                                    | ---  | ---    | -6.0      | A                    |
| $V_{SD}$                     | Diode Forward Voltage <sup>2</sup>             | $V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^\circ\text{C}$                | ---  | ---    | -1.2      | V                    |

**Note :**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



### Typical Characteristics



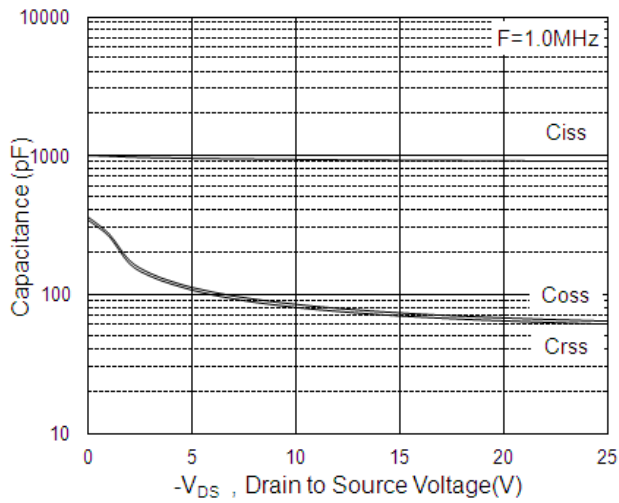


Fig.7 Capacitance

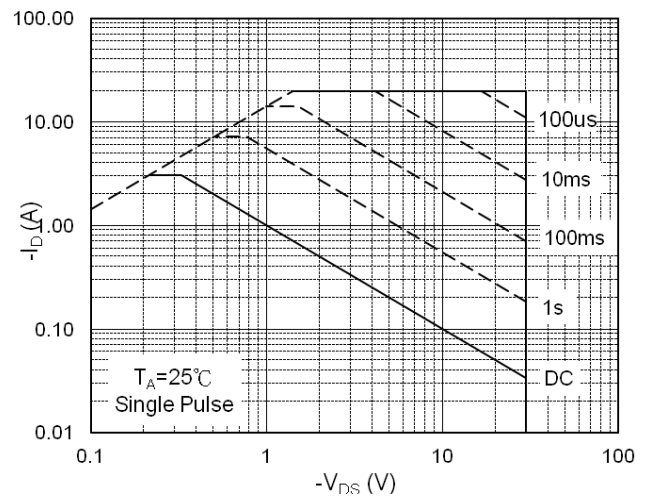


Fig.8 Safe Operating Area

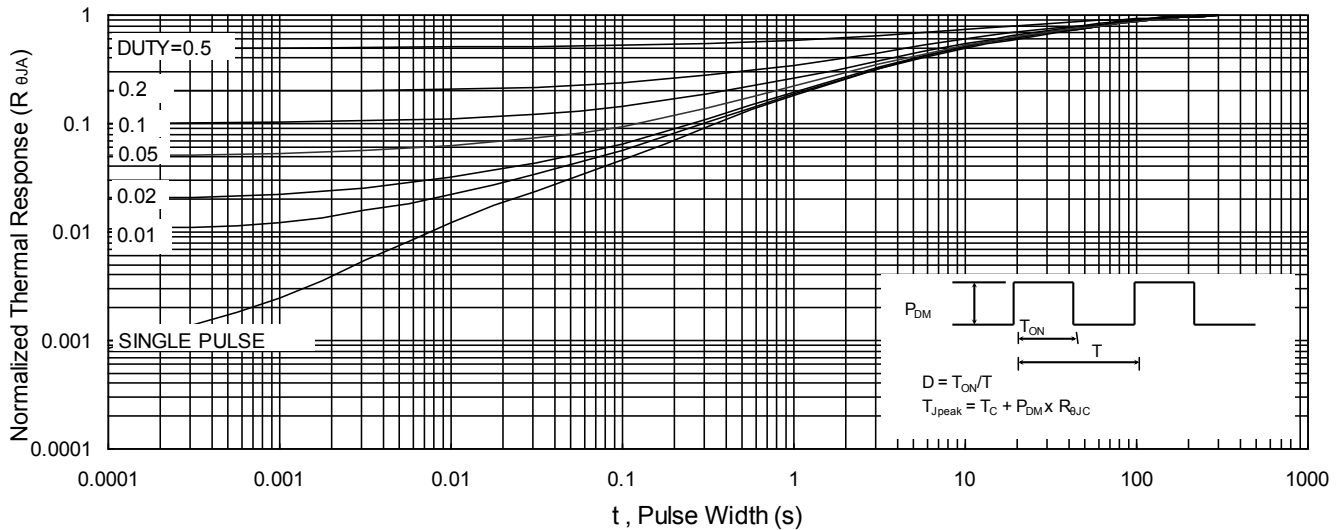


Fig.9 Normalized Maximum Transient Thermal Impedance

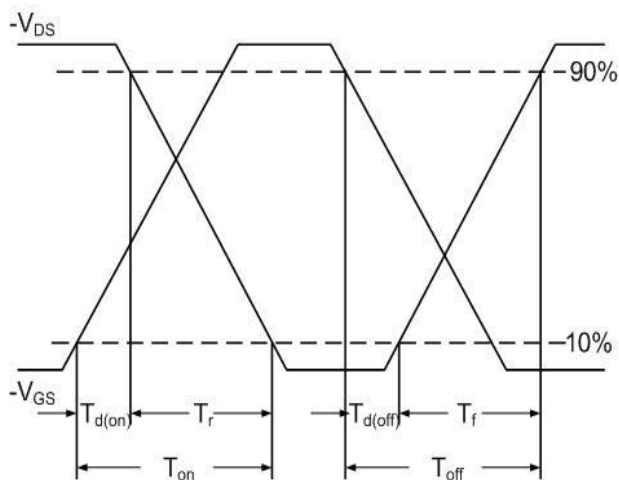


Fig.10 Switching Time Waveform

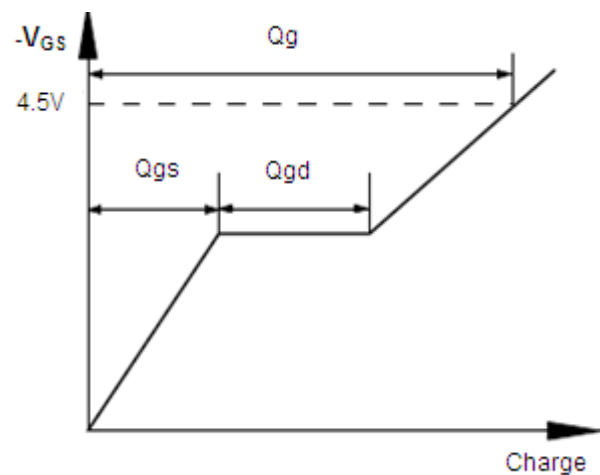
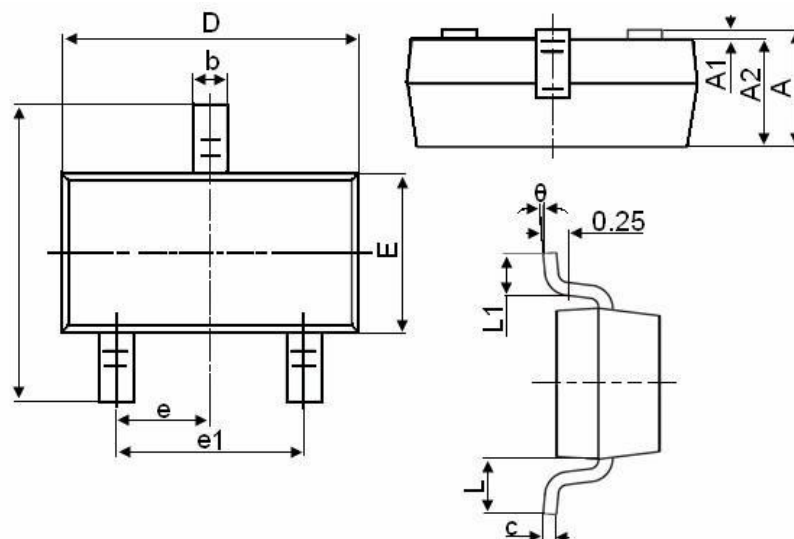


Fig.11 Gate Charge Waveform



## SOT-23-3L Package Information



| Symbol | Dimensions in Millimeters |       |
|--------|---------------------------|-------|
|        | MIN.                      | MAX.  |
| A      | 1.050                     | 1.250 |
| A1     | 0.000                     | 0.100 |
| A2     | 1.050                     | 1.150 |
| b      | 0.300                     | 0.500 |
| c      | 0.100                     | 0.200 |
| D      | 2.800                     | 3.000 |
| E      | 1.500                     | 1.700 |
| E1     | 2.650                     | 2.950 |
| e      | 0.950TYP                  |       |
| e1     | 1.800                     | 2.000 |
| L      | 0.550REF                  |       |
| L1     | 0.300                     | 0.600 |
| θ      | 0°                        | 8°    |



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